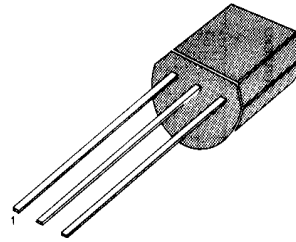


KSP92/93**PNP EPITAXIAL SILICON TRANSISTOR****HIGH VOLTAGE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS (T_A=25℃)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage : KSP92	V _{CBO}	-300	V
: KSP93		-200	V
Collector-Emitter Voltage : KSP92	V _{CEO}	-300	V
: KSP93		-200	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-500	mA
Collector Dissipation (T _A =25℃)	P _C	625	mW
Derate above 25℃		5	mW/℃
Collector Dissipation (T _A =25℃)	P _C	1.5	W
Derate above 25℃		12	mW/℃
Junction Temperature	T _J	150	℃
Storage Temperature	T _{STG}	-55 ~ 150	℃

TO-92



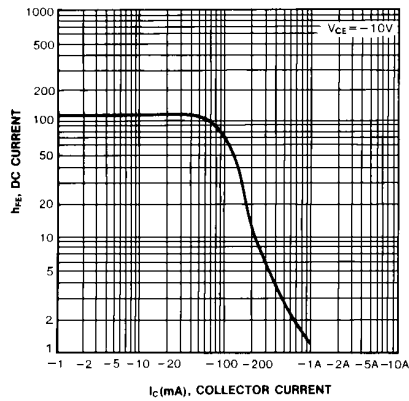
1. Emitter 2. Base 3. Collector

ELECTRICAL CHARACTERISTICS (T_A=25℃)

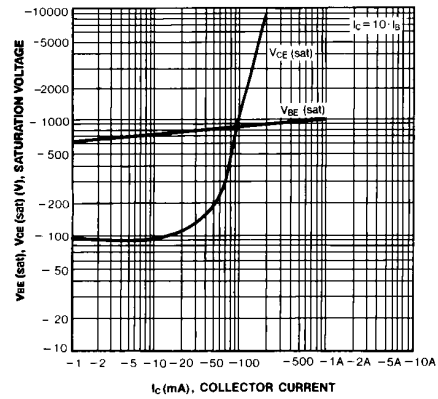
Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = -100μA, I _E =0	-300		V
:KSP92			-200		V
*Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = -1mA, I _B =0	-300		V
:KSP92			-200		V
:KSP93			-5		V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = -100μA, I _C =0			V
Collector Cur-off Current	I _{CBO}	V _{CB} = -200V, I _E =0		-0.25	μA
:KSP92		V _{CB} = -160V, I _E =0		-0.25	μA
:KSP93		V _{EB} = -3V, I _C =0		-0.10	μA
Emitter Cut-off Current	I _{EBO}	V _{CE} = -10V, I _C = -1mA	25		
*DC Current Gain	h _{FE}	V _{CE} = -10V, I _C = -10mA	40		
		V _{CE} = -10V, I _C = -30mA	25		
*Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C = -20mA, I _B = -2mA		-0.50	V
*Base-Emitter Saturation Voltage	V _{BE} (on)	I _C = -20mA, I _B = -2mA		-0.90	V
Current Gain Bandwidth Product	f _T	V _{CE} = -20V, I _C = -10mA	50		MHz
Collector Base Capacitance	C _{CB}	V _{CB} = -20V, I _E =0		6	pF
:KSP92		f=1MHz		8	pF
:KSP93					

* Pulse Test: PW≤ 300μs, Duty Cycle≤ 2%

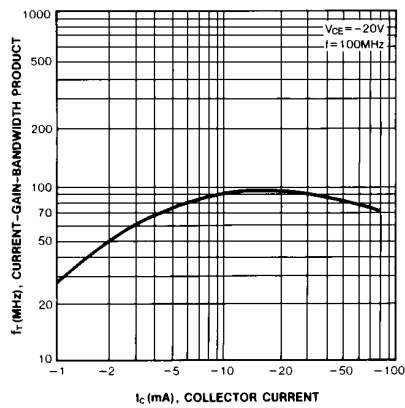
DC CURRENT GAIN



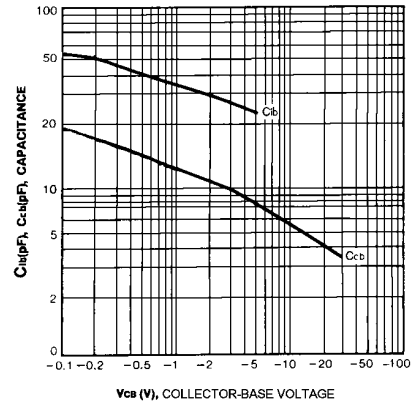
SATURATION VOLTAGES



CURRENT-GAIN-BANDWIDTH PRODUCT



CAPACITANCE



ACTIVE-REGION SAFE OPERATING AREA

